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WOOD, HERRON & EVANS, LLP (NORDSON) 2700 CAREW TOWER 441 VINE STREET			EXAMINER	
			ZERVIGON, RUDY	
CINCINNATI, OH 45202			ART UNIT	PAPER NUMBER
			1792	
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			04/02/2009	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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	Application No.	Applicant(s)	
	10/710,457	CONDRASHOFF ET AL.	
Office Action Summary	Examiner	Art Unit	
	Rudy Zervigon	1792	
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet with the o	correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICATION 136(a). In no event, however, may a reply be ting will apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDONE	N. nely filed the mailing date of this communication. ED (35 U.S.C. § 133).	
Status			
Responsive to communication(s) filed on 18 F This action is FINAL . 2b) ☑ This Since this application is in condition for allowated closed in accordance with the practice under the second	s action is non-final. ince except for formal matters, pro		
Disposition of Claims			
4) Claim(s) 1-7,11-15,17 and 18 is/are pending i 4a) Of the above claim(s) is/are withdra 5) Claim(s) is/are allowed. 6) Claim(s) 1-7,11-15,17 and 18 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/o	wn from consideration.		
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 13 July 2004 is/are: a) Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the E	accepted or b) objected to lead accepted or b) objected to lead and objected to lead and objected to lead and objected to lead and objected if the drawing(s) is objection is required if the drawing(s) is objected to lead accepted to lead and objected to lead accepted to lead a	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
 12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documen 2. Certified copies of the priority documen 3. Copies of the certified copies of the priority documen application from the International Burea * See the attached detailed Office action for a list 	ts have been received. ts have been received in Applicat prity documents have been receive au (PCT Rule 17.2(a)).	ion No ed in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:	ate	

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on February 18, 2009 has been entered.

Claim Rejections - 35 USC § 103

- 2. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
- 3. Claims 1, 5, 6, and 18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Okamura; Hideaki et al. (US 6251216 B1) in view of Stark; Mark M. et al. (US 4786359 A). Okamura teaches an apparatus (Figure 1) for processing a substrate (12; Figure 1; column 5; lines 23-45) with a plasma, comprising: a first electrode (11; Figure 1; column 5; lines 23-45); a second electrode (13; Figure 1; column 5; lines 23-45); a separating member (25; Figure 1 "synthetic quartz"; column 6; lines 1-3) directly contacting said first electrode (11; Figure 1; column 5; lines 23-45) and directly contacting said second electrode (13; Figure 1; column 5; lines 23-45) and forming a sidewall (25; Figure 1 "synthetic quartz"; column 6; lines 1-3) extending from said first electrode (11; Figure 1; column 5; lines 23-45) to said second electrode (13; Figure 1; column 5; lines 23-45) to said second electrode (13; Figure 1; column 5; lines 23-45) to said second electrode (13; Figure 1; column 5; lines 23-45), said separating member (25; Figure 1 "synthetic quartz"; column 6; lines 1-3) composed of a dielectric material capable of electrically isolating said first

electrode (11; Figure 1; column 5; lines 23-45) from said second electrode (13; Figure 1; column 5; lines 23-45); a process region (volume within 25) formed by said separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3), said first electrode (11; Figure 1; column 5; lines 23-45) and said second electrode (13; Figure 1; column 5; lines 23-45); a process gas port (14; Figure 1; column 5; lines 23-45) for introducing a process gas to said processing region (inside volume 25); a vacuum port (22; Figure 1; column 5; lines 23-45) for evacuating said processing region (inside volume 25) to a pressure suitable for generating the plasma from the process gas in said processing region (inside volume 25), a shell (10a,b; Figure 1) surrounding said first electrode (11; Figure 1; column 5; lines 23-45), said second electrode (13; Figure 1; column 5; lines 23-45), and said separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3) - claim 1

Okamura further teaches:

- i. The apparatus (Figure 1) of claim 1 further comprising: a vacuum pump (23; Figure 1; column 5; lines 23-45) coupled with said vacuum port (22; Figure 1; column 5; lines 23-45) and operative for evacuating said processing region (inside volume 25) to said pressure suitable for generating the plasma from the process gas in said processing region (inside volume 25), as claimed by claim 5
- ii. The apparatus (Figure 1) of claim 1 further comprising: a process gas supply (16) coupled with said process gas port (14; Figure 1; column 5; lines 23-45) for introducing the process gas to said processing region (inside volume 25), as claimed by claim 6

iii. The apparatus of claim 1 wherein said first electrode (11; Figure 1; column 5; lines 23-45) is adapted to support the substrate (12; Figure 1; column 5; lines 23-45) in said processing region (inside volume 25), as claimed by claim 18

Okamura does not teach:

- i. a vacuum port (22; Figure 1; column 5; lines 23-45) <u>in said first electrode (11; Figure 1;</u> column 5; lines 23-45) claim 1
- ii. an electrically conductive shell (10a,b; Figure 1) claim 1
- an atmospheric pressure space between said shell (10a,b; Figure 1) and said first electrode (11; Figure 1; column 5; lines 23-45), said second electrode (13; Figure 1; column 5; lines 23-45), and said separating member (25; Figure 1 "synthetic quartz"; column 6; lines 1-3) claim 1. The Examiner argues that because elements 25, 10a, and 10b are all separate units as shown, there should exist a gap at the 25/10a interface and the 25/10b interface. Such a feature is not explicitly shown and neither is the "atmospheric pressure space".

Stark teaches an apparatus (Figure 4) for processing a substrate (44; Figure 4; column 3; lines 9-61) with a plasma, comprising: a first electrode (42; Figure 4; column 3; lines 40-45); a second electrode (48; Figure 4; column 3; lines 20-30); a separating member (51; Figure 4; column 3; line 36) directly contacting said first electrode (42; Figure 4; column 3; lines 40-45) and directly contacting said second electrode (48; Figure 4; column 3; lines 20-30) and forming a sidewall (51; Figure 4; column 3; line 36) extending from said first electrode (42; Figure 4; column 3; lines 40-45) to said second electrode (48; Figure 4; column 3; lines 20-30), said separating member (51; Figure 4; column 3; line 36) composed of a dielectric material ("insulating",

column 3; line 36) capable of electrically isolating said first electrode (42; Figure 4; column 3; lines 40-45) from said second electrode (48; Figure 4; column 3; lines 20-30); a process region (41; Figure 4; column 3; lines 40-45) formed by said separating member (51; Figure 4; column 3; line 36), said first electrode (42; Figure 4; column 3; lines 40-45) and said second electrode (48; Figure 4; column 3; lines 20-30); a process gas port (not shown; column 3; lines 20-30) for introducing a process gas to said processing region (inside volume 25); a vacuum port (not shown; column 3; lines 20-30) in said first electrode (42; Figure 4; column 3; lines 40-45) for evacuating said processing region (inside volume 25) to a pressure suitable for generating the plasma from the process gas in said processing region (inside volume 25).

It would have been obvious to one of ordinary skill in the art at the time the invention was made for Okamura to replace Okamura's first electrode (11; Figure 1; column 5; lines 23-45) with Stark's first electrode (42; Figure 4; column 3; lines 40-45) having a vacuum port (not shown; column 3; lines 20-30).

It would have been obvious to one of ordinary skill in the art at the time the invention was made for Okamura to establish an "atmospheric pressure space" between 25/10a interface and the 25/10b interface *based on the process for making* Okamura's apparatus.

Motivation for Okamura to replace Okamura's first electrode (11; Figure 1; column 5; lines 23-45) with Stark's first electrode (42; Figure 4; column 3; lines 40-45) having a vacuum port (not shown; column 3; lines 20-30) is for generating lower pressure prococesses.

Motivation for Okamura to establish an "atmospheric pressure space" between 25/10a interface and the 25/10b interface *based on the process for making* Okamura's apparatus is for reducing product-by-process manufacturing costs.

- 4. Claims 2, and 3 are rejected under 35 U.S.C. 103(a) as being unpatentable over Okamura; Hideaki et al. (US 6251216 B1) and Stark; Mark M. et al. (US 4786359 A) in view of Shan; Hong Ching et al. (US 5891350 A). Okamura and Stark are described above. Okamura and Stark do not teach:
 - i. The apparatus (Figure 1) of claim 1 further comprising: a vacuum manifold coupled with said vacuum port (22; Figure 1; column 5; lines 23-45), said vacuum manifold being electrically isolated from said first electrode (11; Figure 1; column 5; lines 23-45) and said second electrode (13; Figure 1; column 5; lines 23-45), as claimed by claim 2
 - ii. The apparatus (Figure 1) of claim 2 wherein said vacuum manifold includes an enclosed volume proximate to said vacuum port (22; Figure 1; column 5; lines 23-45) and further comprising: an insert of an electrically insulating material ("synthetic quartz"; column 6; lines 1-3) positioned inside said enclosed volume, said insert including a first plurality of passages coupling said vacuum manifold with said vacuum port (22; Figure 1; column 5; lines 23-45), as claimed by claim 3

Shan teaches:

iv. The apparatus (Figure 1,3 - see common numbers) of claim 1 further comprising: a vacuum manifold (70, Figure 4; column 15; line 62 - column 16, line25) coupled with said vacuum port (50, Figure 1,3; column 3; lines 30-45), said vacuum manifold (70, Figure 4; column 15; line 62 - column 16, line25) being electrically isolated from said first electrode (30; Figure 1,3; column 3; lines 34-41) and said second electrode (24," Aanode"; Figure 1,3; column 7; lines 1-15), as claimed by claim 2

v. The apparatus (Figure 1,3 - see common numbers) of claim 2 wherein said vacuum manifold (70, Figure 4; column 15; line 62 - column 16, line25) includes an enclosed volume proximate to said vacuum port (50, Figure 1,3; column 3; lines 30-45) and further comprising: an insert (74, 76, or 78; Figure 4; column 15; line 62 - column 16, line25) of an electrically insulating material (column 16, lines 16-25) positioned inside said enclosed volume, said insert (74, 76, or 78; Figure 4; column 15; line 62 - column 16, line25) including a first plurality of passages (72 in 74; Figure 4; column 15; line 62 - column 16, line25) coupling said vacuum manifold (70, Figure 4; column 15; line 62 - column 16, line25) with said vacuum port (50, Figure 1,3; column 3; lines 30-45), as claimed by claim 3

It would have been obvious to one of ordinary skill in the art at the time the invention was made for Okamura to add Shan's exhaust inserts (74, 76, or 78; Figure 4; column 15; line 62 - column 16, line25).

Motivation for Okamura to add Shan's exhaust inserts (74, 76, or 78; Figure 4; column 15; line 62 - column 16, line25) is for "reducing the deposition of unwanted particles on the exhaust pump componentd" as taught by Shan (abstract), and for "protecting the top perimeter of the cathode from exposure to plasma" as taught by Shan (column 4; lines 21-25).

5. Claims 15-17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Okamura; Hideaki et al. (US 6251216 B1) and Stark; Mark M. et al. (US 4786359 A) in view of Suntola; Tuomo et al. (US 5711811 A) and Maher, Jr.; Joseph A. et al. (US 4381965 A). Okamura and Stark are disccused above. Okamura and Stark do not teach:

> i. An apparatus (Figure 1) for plasma processing a plurality of substrates (12; Figure 1; column 5; lines 23-45), the apparatus comprising: a first electrode (11; Figure 1; column 5; lines 23-45); a second electrode (13; Figure 1; column 5; lines 23-45) positioned with a spaced apart relationship relative to said first electrode (11; Figure 1; column 5; lines 23-45); a third electrode positioned between said first electrode (11; Figure 1; column 5; lines 23-45) and said second electrode (13; Figure 1; column 5; lines 23-45); a first separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3) directly contacting said first electrode (11; Figure 1; column 5; lines 23-45) and directly contacting said third electrode forming a first sidewall extending between said first electrode (11; Figure 1; column 5; lines 23-45) and said third electrode, said first electrode (11; Figure 1; column 5; lines 23-45) configured to support one of the plurality of substrates (12; Figure 1; column 5; lines 23-45) in said first processing region (inside volume 25) for plasma processing, and said first separating member (25; Figure 1 -"synthetic quartz"; column 6; lines 1-3) comprising a dielectric material ("synthetic quartz"; column 6; lines 1-3) for electrically isolating said first electrode (11; Figure 1; column 5; lines 23-45) from said third electrode; a first processing region formed by said first separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3), said first electrode (11; Figure 1; column 5; lines 23-45), and said third electrode; a second separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3) directly contacting said second electrode (13; Figure 1; column 5; lines 23-45) and directly contacting said third electrode forming a second sidewall extending between said second electrode (13; Figure 1; column 5; lines 23-45) and said third electrode, said second

> electrode configured to support one of the plurality of substrates (12; Figure 1; column 5; lines 23-45) in said second processing region (inside volume 25) for plasma processing, and said second separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3) comprising a dielectric material for electrically isolating said second electrode (13; Figure 1; column 5; lines 23-45) from said third electrode; a second processing region formed by said second member, said second electrode (13; Figure 1; column 5; lines 23-45), and said third electrode at least one process gas port (14; Figure 1; column 5; lines 23-45) configured for introducing a process gas to said first processing region (inside volume 25) and second processing region (inside volume 25); a vacuum port (22; Figure 1; column 5; lines 23-45) in said first electrode (11; Figure 1; column 5; lines 23-45) for evacuating said first and second processing regions (inside volume 25) to a subatmospheric pressure suitable for generating the plasma from the process gas in said first processing region (inside volume 25) and said second processing region (inside volume 25), an electrically conductive shell (10a,b; Figure 1) surrounding said first electrode (11; Figure 1; column 5; lines 23-45), said second electrode (13; Figure 1; column 5; lines 23-45), said third electrode, said first separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3), and said second separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3); and an atmospheric pressure space between said shell (10a,b; Figure 1) and said first electrode (11; Figure 1; column 5; lines 23-45), said second electrode (13; Figure 1; column 5; lines 23-45), said third electrode, said first separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3), and said

second separating member (25; Figure 1 - "synthetic quartz"; column 6; lines 1-3) - claim

ii. The apparatus (Figure 1) of claim 15 wherein said first electrode (11; Figure 1; column 5; lines 23-45) includes a first process gas port (14; Figure 1; column 5; lines 23-45) for introducing the process gas to said first processing region (inside volume 25) and said third electrode includes a second process gas port (14; Figure 1; column 5; lines 23-45) for introducing the process gas to said second processing region (inside volume 25), as claimed by claim 17

Suntola teaches:

i. An apparatus (Figure 3) for plasma (column 1; lines 42-44) processing a plurality of substrates (37; Figure 3), comprising: a first separating member (32; Figure 3; column 11, lines 23-27) for forming a vacuum-tight seal between a first chamber (38; Figure 3) and a second chamber (38; Figure 3) and defining a first evacuatable processing region (38; Figure 3) between a first chamber (38; Figure 3) and a second chamber (38; Figure 3), a first chamber (38; Figure 3) configured to support one of the plurality of substrates (37; Figure 3) in first processing region (38; Figure 3) for plasma (column 1; lines 42-44) processing, and said first separating member (32; Figure 3; column 11, lines 23-27) electrically isolating a first chamber (38; Figure 3) from a second chamber (38; Figure 3); a second separating member (32; Figure 3; column 11, lines 23-27) for forming a vacuum-tight seal between a third chamber (38; Figure 3) and a second chamber (38; Figure 3) between a third chamber (38; Figure 3) and a second chamber (38; Figure 3).

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Figure 3) configured to support one of the plurality of substrates (37; Figure 3) in said second processing region (38; Figure 3) for plasma (column 1; lines 42-44) processing, and said second separating member (32; Figure 3; column 11, lines 23-27) electrically isolating a third chamber (38; Figure 3) from a second chamber (38; Figure 3); at least one process gas port (28, 30; Figure 3) for introducing a process gas to first processing region (38; Figure 3) and second processing region (38; Figure 3); and a vacuum port (25; Figure 3) for evacuating said processing region (inside volume 25) to a pressure suitable for generating the plasma (column 1; lines 42-44) from the process gas in first processing region (38; Figure 3) and said second processing space (38; Figure 3) - claim

ii. The apparatus (Figure 3) of claim 15 wherein a first chamber (38; Figure 3) includes a first process gas port (28, 30; Figure 3) for introducing the process gas to first processing region (38; Figure 3) and a second chamber (38; Figure 3) includes a second process gas port (28, 30; Figure 3) for introducing the process gas to said second process region (volume within 25), as claimed by claim 17

Maher teaches a wafer plasma processing apparatus (Figure 4) including plural parallel electrodes 19a,b-25a,b each interposed between insulating dielectric layers 19c-25c.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to add Suntola's apparatus (Figure 3) with Maher's plasma generating means to Okamura's apparatus.

Motivation to add Suntola's apparatus (Figure 3) with Maher's plasma generating means to Okamura's apparatus includes, among plural motivations, for plasma processing as taught by

Suntola (column 1; lines 42-44), and for processing plural substrates for greater through-put compared to Okamura as taught by Suntola.

- 6. Claims 4, 7, and 11-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Okamura; Hideaki et al. (US 6251216 B1) and Stark; Mark M. et al. (US 4786359 A) in view of Shan; Hong Ching et al. (US 5891350 A) and Hirooka; Takaaki (US 6700089 B1). Okamura, Stark, and Shan are discussed above. Okamura, Stark, and Shan do not teach:
 - i. The apparatus (Figure 1) of claim 3 wherein said vacuum port (22; Figure 1; column 5; lines 23-45) is defined by a second plurality of passages extending through said first electrode (11; Figure 1; column 5; lines 23-45) and registered with said first plurality of passages, as claimed by claim 4
 - ii. The apparatus (Figure 1) of claim 1 wherein said second electrode (13; Figure 1; column 5; lines 23-45) includes a plurality of openings arranged in a pattern effective for communicating process gas from said process gas port (14; Figure 1; column 5; lines 23-45) to said processing region (inside volume 25), as claimed by claim 7
- iii. The apparatus (Figure 1) of claim 1 wherein said shell (10a,b; Figure 1) includes a base and a lid movable relative to said lid between opened and closed positions for accessing said processing region (inside volume 25), said lid carrying said second electrode for movement relative to said base, as claimed by claim 11
- The apparatus (Figure 1) of claim 1 further comprising a coolant port in said lid for iv. supplying a flow of a coolant fluid to said atmospheric pressure space for cooling said first electrode (11: Figure 1: column 5: lines 23-45) and said second electrode (13: Figure 1; column 5; lines 23-45), as claimed by claim 12

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 - The apparatus (Figure 1) of claim 1 wherein said second electrode (13; Figure 1; column v. 5; lines 23-45) includes said process gas port (14; Figure 1; column 5; lines 23-45), as claimed by claim 13
- vi. The apparatus (Figure 1) of claim 13 wherein said second electrode (13; Figure 1; column 5; lines 23-45) includes a plurality of gas openings coupled with said process gas port (14; Figure 1; column 5; lines 23-45), said plurality of gas openings positioned in said second electrode (13; Figure 1; column 5; lines 23-45) to distribute process gas across a confronting surface of the substrate (12; Figure 1; column 5; lines 23-45), as claimed by claim 14

Hirooka teaches a plasma processing apparatus (Figure 1,2) including:

- i. The apparatus (Figure 1,2) of claim 3 wherein a vacuum port (128; Figure 1,2) is defined by a second plurality of passages (126; Figure 1,2) extending through a first electrode (108+126; Figure 1) - claim 4
- The apparatus (Figure 1,2) of claim 1 wherein a second electrode (124; Figure 2) includes ii. a plurality of openings (124a; Figure 2) arranged in a pattern effective for communicating process gas from a process gas port (194; Figure 2) to a processing region (102; Figure 2), as claimed by claim 7
- iii. The apparatus (Figure 1,2) of claim 10 wherein a enclosure includes a base (104; Figure 2) and a lid (206; Figure 2.3a) movable relative to a lid (206; Figure 2.3a) between opened and closed positions for accessing a processing region (102; Figure 2), a lid (206; Figure 2,3a) carrying a first electrode (108+126; Figure 1) for movement relative to a base (104; Figure 2), as claimed by claim 11

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- iv. The apparatus (Figure 1,2) of claim 10 further comprising a coolant port (172c; Figure 2) in a lid (206; Figure 2,3a) for supplying a flow of a coolant fluid to a air gap (172c; Figure 2) for cooling a first electrode (108+126; Figure 1) and a second electrode (124; Figure 2), as claimed by claim 12
- The apparatus (Figure 1,2) of claim 1 wherein a first electrode (108+126; Figure 1) v. includes a vacuum port (128; Figure 1,2) and a second electrode (124; Figure 2) includes a process gas port (194; Figure 2), as claimed by claim 13
- The apparatus (Figure 1,2) of claim 13 wherein a second electrode (124; Figure 2) vi. includes a plurality of gas openings (124a; Figure 2) coupled with a process gas port (194; Figure 2), a plurality of gas openings (124a; Figure 2) positioned in a second electrode (124; Figure 2) to distribute process gas across a confronting surface of the substrate (12; Figure 1; column 5; lines 23-45), as claimed by claim 14

It would have been obvious to one of ordinary skill in the art at the time the invention was made to replace Okamura's lid and lower electrode with Hirooka's lid and lower electrode.

Motivation to replace Okamura's lid and lower electrode with Hirooka's lid and lower electrode is for improved hermiticity and operating speed (Hirooka:column 2; lines 10-27), and for wafer temperature control (Hirooka:column 7; lines 1-3), respectively.

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Response to Arguments

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7. Applicant's arguments with respect to claims 1-7, 11-15, 17, 18 have been considered but

are moot in view of the new grounds of rejection.

8. Applicant's arguments are centered on the Examiner's prior rejection under 102 based on

Okamura alone. In view of Applicant's amendments, the Examiner has withdrawn the

anticipation under Okamura in favor of the above new grounds of rejection.

9. Applicant's amendments are each addressed above in the body of the Examiner's newly

proposed rejections.

Conclusion

10. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Examiner Rudy Zervigon whose telephone number is (571) 272-

1442. The examiner can normally be reached on a Monday through Friday schedule from 9am

through 5pm. The official fax phone number for the 1792 art unit is (571) 273-8300. Any Inquiry

of a general nature or relating to the status of this application or proceeding should be directed to

the Chemical and Materials Engineering art unit receptionist at (571) 272-1700. If the examiner

can not be reached please contact the examiner's supervisor, Parviz Hassanzadeh, at (571) 272-

1435

/Rudy Zervigon/

Primary Examiner, Art Unit 1792